

DMTH6004LPSQ

60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	Rds(on) Max	I _D Max Tc = +25°C (Note 5)	
60)/	3.1mΩ @ V _{GS} = 10V	100A	
60V	4.5mΩ @ V _{GS} = 4.5V	100A	

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Primary switches in isolated DC-DC
- Synchronous rectifiers
- Load switches

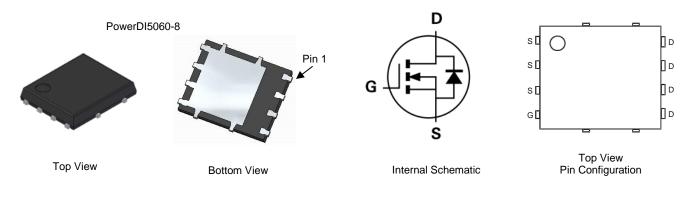
Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Low RDS(ON) Minimizes Power Losses
- Low Qg Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH6004LPSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/guality/product-definitions/

Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (€3)
- Weight: 0.097 grams (Approximate)



Ordering Information (Note 4)

Part Number	Backage	Packing		
Part Number	Package	Qty.	Carrier	
DMTH6004LPSQ-13	PowerDI5060-8	2,500	Tape & Reel	

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

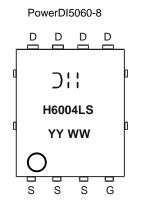
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

5. Limited by package.



Marking Information



) | |= Manufacturer's Marking H6004LS = Product Type Marking Code YYWW = Date Code Marking YY = Year Code (ex: 24 = 2024)WW = Week Code (01 to 53)

Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		VDSS	60	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Note 6)	T _A = +25°C T _A = +70°C	ID	22 16	A
Continuous Drain Current (Notes 5 & 7)	T _C = +25°C T _C = +100°C	lo	100 100	А
Maximum Continuous Body Diode Forward Current (Note 6)		ls	100	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	400	А
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		lsм	400	A
Avalanche Current, L = 0.2mH		las	40	А
Avalanche Energy, L = 0.2mH		Eas	160	mJ

Thermal Characteristic

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	PD	2.6	W
Thermal Resistance, Junction to Ambient (Note 6)		Reja	47	°C/W
Total Power Dissipation (Note 7)	Tc = +25°C	PD	138	W
Thermal Resistance, Junction to Case (Note 7)		R _{0JC}	0.9	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Notes:

Limited by package.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

7. Thermal resistance from junction to soldering point (on the exposed drain pad).



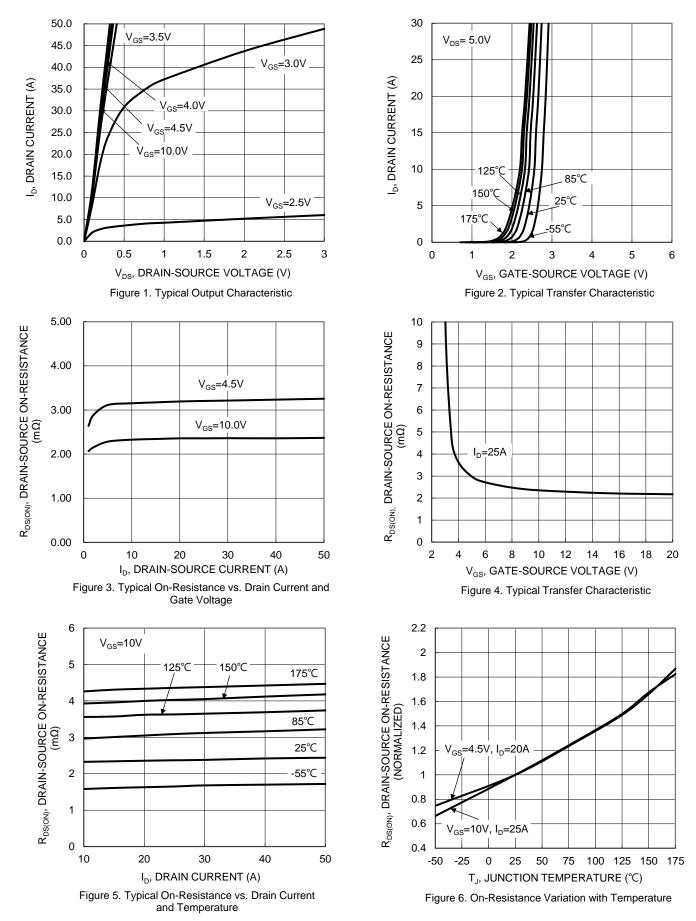
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)		•	•			·	
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	—	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	Vgs(th)	1	—	3	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Deserve	—	2.5	3.1	mΩ	$V_{GS} = 10V, I_D = 25A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	—	3.3	4.5	mΩ	$V_{GS} = 4.5V, I_D = 20A$	
Diode Forward Voltage	Vsd	_	_	1.3	V	V _{GS} = 0V, I _S = 25A	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	—	5399	—		$V_{DS} = 30V, V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss	—	1306	_	pF		
Reverse Transfer Capacitance	Crss	—	92	_			
Gate Resistance	Rg	—	0.64	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	—	78.3	_			
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	38.5	—	nC	VDD = 30V, ID = 25A	
Gate-Source Charge	Qgs	_	10.2	—	nc		
Gate-Drain Charge	Q _{gd}	—	20.4	_			
Turn-On Delay Time	tD(ON)	—	9.9	_		$V_{DD} = 30V, V_{GS} = 10V$ $I_D = 25A, R_g = 3.5\Omega$	
Turn-On Rise Time	tR	—	17.7	_			
Turn-Off Delay Time	tD(OFF)	—	53.5	—	ns		
Turn-Off Fall Time	tF	—	32.9				
Body Diode Reverse Recovery Time	trr	—	49.7		ns		
Body Diode Reverse Recovery Charge	Qrr	—	78.9	_	nC	IF = 25A, di/dt = 100A/μs	

 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to production testing. Notes:

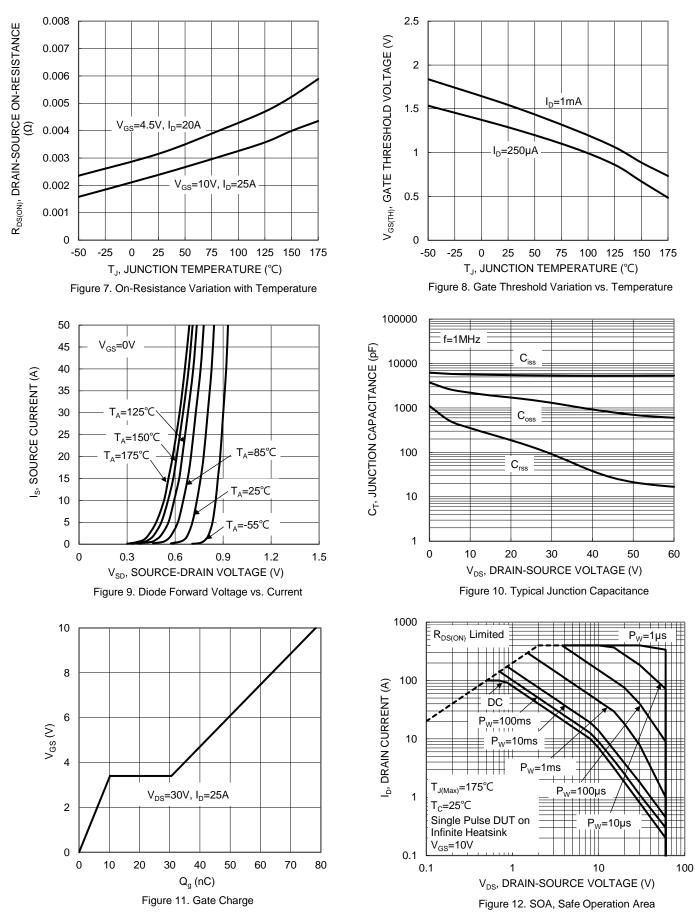


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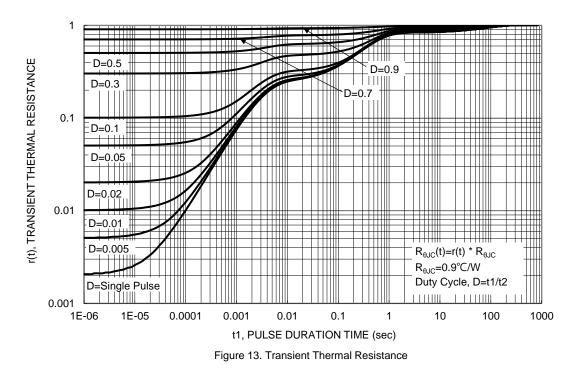


DMTH6004LPSQ Document number: DS38165 Rev. 4 - 2

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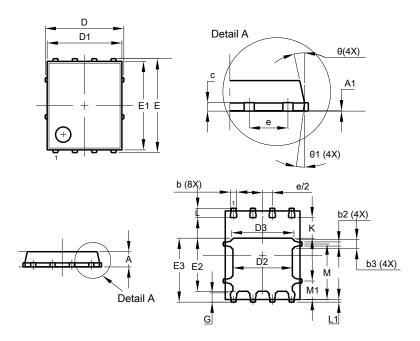




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

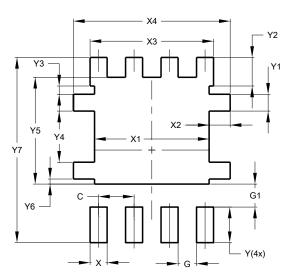


		15000 0			
PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
c	0.230	0.330	0.277		
D		5.15 BSC			
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	(6.15 BSC	;		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
κ	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610



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